

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



February 2013

BSS84

P-Channel Enhancement Mode Field-Effect Transistor

Features

- -0.13 A, -50 V, $R_{DS(ON)} = 10 \Omega$ at $V_{GS} = -5 V$
- Voltage-Controlled P-Channel Small-Signal Switch
- High-Density Cell Design for Low R_{DS(ON)}
- High Saturation Current





Description

This P-channel enhancement-mode field-effect transistor is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process minimizes on-state resistance and to provide rugged and reliable performance and fast switching. The BSS84 can be used, with a minimum of effort, in most applications requiring up to 0.13 A DC and can deliver current up to 0.52 A. This product is particularly suited to low-voltage applications requiring a low-current high-side switch.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain-Source Voltage		-50	V
V_{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current ⁽¹⁾	Continuous	-0.13	Α
		Pulsed	-0.52	Α
_	Maximum Power Dissipation ⁽¹⁾		0.36	W
P_D	Derate Above 25°C		2.9	mW / °C
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C
TL	Maximum Lead Temperature for Soldering Purposes 1/16" from Case for 10 Seconds		300	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient ⁽¹⁾	350	°C/W

Note:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the user's board design.



a) 350°C/W when mounted on a minimum pad

Scale 1: 1 on letter-size paper.

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
SP	BSS84	7"	8mm	3000

Electrical Characteristics(2)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-50			V
ΔBV_{DSS}	Breakdown Voltage Temperature	$I_D = -250 \mu A$		4.0		
<u></u> ΔT _J	Coefficient	Referenced to 25°C		-4 8		mV / ℃
		$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}$			-15	uΑ
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V},$				^
	Ü	T _J = 125°C			-60	μΑ
I_{GSS}	Gate-Body Leakage.	$V_{GS} = \pm 20 \text{ V}, \ V_{DS} = 0 \text{ V}$			±10	nA
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-50			V
On Char	acteristics ⁽²⁾					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -1$ mA	-0.8	-1.7	-2	V
V _{GS(TH)}	Gate Threshold Voltage	$I_D = -1 \text{ mA},$				1/100
TJ	Temperature Coefficient	Referenced to 25°C		3		mV / ℃
1	Static Drain–Source On–Resistance	$V_{GS} = -5 \text{ V}, I_D = -0.10 \text{ A}$		1.2	10.0	Ω
R _{DS(on)}		$V_{GS} = -5 \text{ V}, I_D = -0.10 \text{ A},$		1.9	17.0	Ω
		T _J = 125°C		1.9	17.0	22
I _{D(on)}	On–State Drain Current	$V_{GS} = -5 \text{ V}, V_{DS} = -10 \text{ V}$	-0.6			Α
g FS	Forward Transconductance	$V_{DS} = -25 \text{ V}, I_{D} = -0.10 \text{ A}$	0.05	0.60		S
_	Characteristics				1	
C _{ISS}	Input Capacitance	$V_{DS} = -25 \text{ V},$		73		pF
Coss	Output Capacitance	$V_{GS} = 0 V$		10		pF
C_{RSS}	Reverse Transfer Capacitance	f = 1.0 MHz		5		pF
R _G	Gate Resistance	$V_{GS} = -15 \text{ mV}, f = 1.0 \text{ MHz}$		9		Ω
Switchin	g Characteristics ⁽²⁾					
t _{d(on)}	Turn-On Delay			2.5	5.0	ns
t _r	Turn-On Rise Time	$V_{DD} = -30 \text{ V}, I_D = -0.27 \text{ A},$		6.3	13.0	ns
t _{d(off)}	Turn-Off Delay	$V_{GS} = -10 \text{ V}, R_{GEN} = 6$		10	20	ns
t _f	Turn-Off Fall Time			4.8	9.6	ns
Q_g	Total Gate Charge	$V_{DS} = -25 \text{ V}, I_{D} = -0.10 \text{ A},$		0.9	1.3	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = -25 \text{ V}, \text{ 1D} = -0.10 \text{ A},$ $V_{GS} = -5 \text{ V}$		0.2		nC
Q_{gd}	Gate-Drain Charge			0.3		nC
Drain-Sc	ource Diode Characteristics and	Maximum Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current		. //		-0.13	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = - 0.26 A ⁽²⁾		-0.8	-1.2	V
t _{RR}	Diode Reverse-Recovery Time	I _F = -0.1 A,		10		ns
	Diode Reverse-Recovery Charge	$d_{iF} / d_t = 100 \text{ A} / \mu s^{(2)}$	-	3		

Note:

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Characteristics

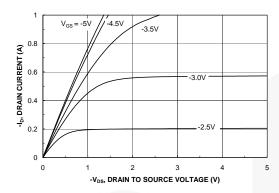


Figure 1. On-Region Characteristics

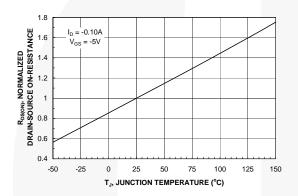


Figure 3. On-Resistance Variation with Temperature

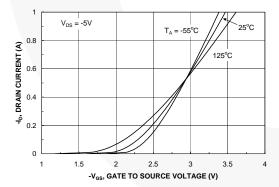


Figure 5. Transfer Characteristics

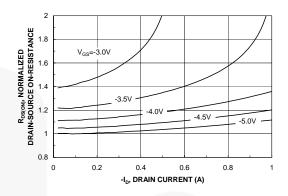


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

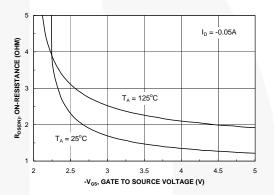


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

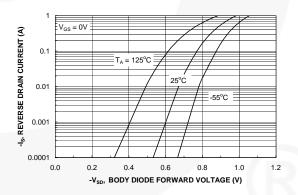


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics (Continued)

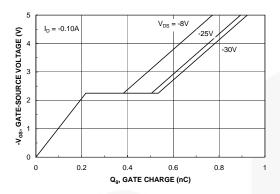


Figure 7. Gate Charge Characteristics

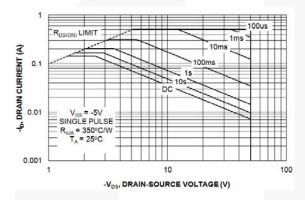


Figure 9. Maximum Safe Operating Area

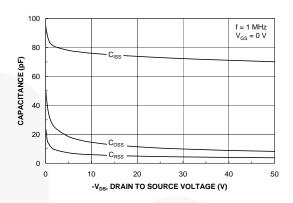


Figure 8. Capacitance Characteristics

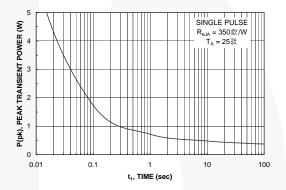


Figure 10. Single-Pulse Maximum Power Dissipation

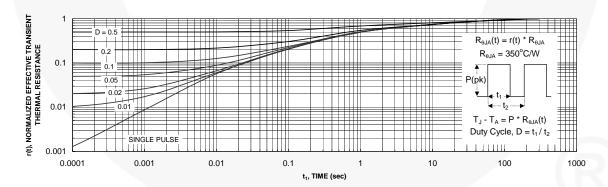


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described on page 1. Transient thermal response will change depending on the circuit board design.

Physical Dimension

SOT-23 3L

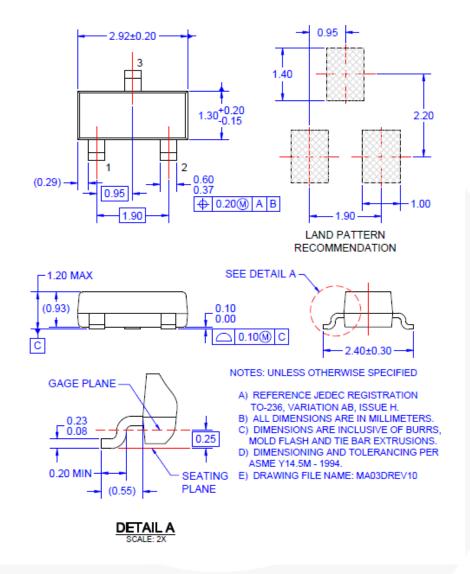


Figure 12. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings: http://www.fairchildsemi.com/packaging/.

For current tape and reel specifications, visit Fairchild Semiconductor's online packaging area: http://www.fairchildsemi.com/packaging/tr/SOT23-3L tr.pdf.



(h

TRADEMARKS

CorePLUS™

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

 $\begin{array}{lll} \mathsf{CorePOWER}^{\intercal \mathsf{M}} & \mathsf{Green} \; \mathsf{FPS}^{\intercal \mathsf{M}} \; \mathsf{e}\text{-}\mathsf{Series}^{\intercal \mathsf{M}} \\ \mathsf{CROSSVOLT}^{\intercal \mathsf{M}} & \mathsf{Gmax}^{\intercal \mathsf{M}} \\ \mathsf{CTL}^{\intercal \mathsf{M}} & \mathsf{GTO}^{\intercal \mathsf{M}} \\ \end{array}$

Current Transfer Logic™ IntelliMAX™
DEUXPEED® ISOPLANAR™
Notice Small Continue Cont

 Dual Cool™
 Making Small Speakers Sound Louder

 EcoSPARK®
 and Better™

Green FPS™

ECOSPARK and Better "

EfficientMax™ MegaBuck™

ESBC™ MICROCOUPLER™

MicroFET™

Fairchild® MicroFET™

Fairchild Semiconductor®
FACT Quiet Series™ MotionMax™
FAST® MWSaver™
FastvCore™ OptoHiT™
FETBench™ OPTOLOGIC®

PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™

SMART START™ Solutions for Your Success™

SPM[®]
STEALTH™
SuperFET[®]
SuperSOT™ 3

SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™ Sync-Lock™

SYSTEM

GENERAL®*

TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TinyYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™

TriFault Detect™
TRUECURRENT®*

µSerDes™

SerDes*
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

OPTOPLANAR®

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a)
 are intended for surgical implant into the body or (b) support or
 sustain life, and (c) whose failure to perform when properly used in
 accordance with instructions for use provided in the labeling, can be
 reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Definition of Terms					
Datasheet Identification	Product Status	Definition			
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.			
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.			

Rev. 164

^{*} Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative